

# Internally Trimmed Precision IC Multiplier

**AD534** 

### 1.0 **SCOPE**

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at <a href="http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die Broc.pdf">http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die Broc.pdf</a> is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at <a href="https://www.analog.com/AD534">www.analog.com/AD534</a>

**2.0 Part Number.** The complete part number(s) of this specification follow:

Part Number Description

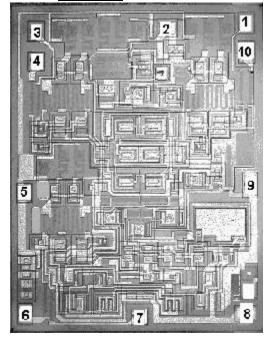
AD534-000C Internally Trimmed Precision IC Multiplier

## 3.0 <u>Die Information</u>

### 3.1 <u>Die Dimensions</u>

Die Size	Die Thickness	Bond Pad Metalization
80 mil x 102 mil	19 mil ± 2 mil	Al/Cu

# 3.2 <u>Die Picture</u>



- X2
   SF
- 3. Y1
- 4. Y2
- 5. -Vs
- 6. Z2
- 7. Z1
- 8. OUT
- 9. +V<sub>S</sub>
- 10. X1

ASD0012805 Rev. G

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# 3.3 Absolute Maximum Ratings 1/

Absolute Maximum Ratings Notes:

1/ Stresses above the absolute maximum rating may cause permanent damage to the device.
Extended operation at the maximum levels may degrade performance and affect reliability.

# 4.0 <u>Die Qualification</u>

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Sample Size and Qual Acceptance Criteria 10/0
- (b) Qual Sample Package DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I - Dice Electrical Characteristics						
Parameter	Symbol	Symbol Conditions 1/			Units	
Relative Accuracy <u>2/</u>		$V_X = -10V, -10V, +10V,$ +10V; $V_Y = -10V, -10V,$ +10V, +10V		±1	%	
Nonlinearity, X Input	NLx	$V_X = 20V p-p, V_Y = +10V$		±0.6	%	
Nonlinearity, Y Input	NL <sub>Y</sub>	$V_Y = 20V \text{ p-p, } V_X = +10V$		±0.6	%	
Output Offset Voltage	Vos	$V_X = V_Y = V_Z = 0V$		±30	mV	
Offset Voltage (X)	Vosx	$V_X = V_Z = 0V, V_Y = \pm 10V$		±20	mV	
Offset Voltage (Y)	V <sub>osy</sub>	$V_Y = V_Z = 0V, V_X = \pm 10V$		±20	mV	
Input Bias Current (X, Y, or Z)	I <sub>IB</sub>	$V_X = V_Y = V_Z = 0V$		±2	μΑ	
Input Offset Current	los	$V_X = V_Y = V_Z = 0V$		±2	μΑ	
Positive Supply Current	lcc	$R_L = No Load$		6	mA	
Negative Supply Current	I <sub>EE</sub>	$R_L = No Load$		6	mA	
Common Mode Rejection Ratio	CMR <sub>X</sub>	$-10V \le V_X \le +10V,$ $V_Y = +10V$	70		dB	
	CMR <sub>Y</sub>	$-10V \le V_Y \le +10V$ , $V_X = +10V$	70		as	
Output Voltage Swing	V <sub>OP</sub>		±11		٧	

Table I Notes:

 $<sup>1/</sup>V_S = \pm 15V$ ,  $T_A = +25$ °C unless otherwise specified.

<sup>2/</sup> Figures given are % of Full Scale, ±10V (i.e., 0.01% = 1mV).

Table II - Electrical Characteristics for Qual Samples							
Parameter	Symbol	Conditions <u>1/</u>	Sub- groups	Limit Min	Limit Max	Units	
Relative Accuracy <u>2/</u>	R <sub>A</sub>	$V_X = -10V, -10V, +10V, +10V; V_Y = -10V, -10V, +10V, +10V$	1, 2, 3		±1	%FS	
Multiplier Accuracy Drift	$TC_MA$		2, 3		±0.01	%/°C	
Nonlinearity, X Input	NLx	$V_X = 20V \text{ p-p, } V_Y = +10V$	1		±0.6	%	
Nonlinearity, Y Input	NLx	$V_Y = 20V p-p, V_X = +10V$	1		±0.6	%	
Outrout Offset Valte se	Vos	V V V 0V	1		±30	mV	
Output Offset Voltage		$V_X = V_Y = V_Z = 0V$	2, 3		±45		
Output Offset Voltage Drift	ΔV <sub>OS</sub> /ΔΤ		2, 3		±300	μV/°C	
Offset Voltage (X)	$V_{OSX}$	$V_X = V_Z = 0V, V_Y = \pm 10V$	1		±20	mV	
Offset Voltage (Y)	$V_{OSY}$	$V_Y = V_Z = 0V, V_X = \pm 10V$	1		±20	mV	
Input Bias Current (X, Y, or Z)	I <sub>IВ</sub>	$V_X = V_Y = V_Z = 0V$	1		±2	μΑ	
Input Offset Current	los	$V_X = V_Y = V_Z = 0V$	1		±2	μΑ	
Positive Supply Current	I <sub>CC</sub>	R <sub>L</sub> = No Load	1		6	mA	
Negative Supply Current	lee	R <sub>L</sub> = No Load	1		6	mA	
Common Made Deigntion Dette	$CMR_X$	$-10V \le V_X \le +10V,$ $V_Y = +10V$	4	70		dB	
Common Mode Rejection Ratio	$CMR_Y$	$-10V \le V_Y \le +10V,$ $V_X = +10V$	4	70			
Output Voltage Swing	V <sub>OP</sub>		1, 2, 3	±11		V	

# Table II Notes:

 $<sup>\</sup>underline{1/}$  V<sub>S</sub> = ±15V, unless otherwise specified.

 $<sup>\</sup>underline{2/}$  Figures given are % of Full Scale, ±10V (i.e., 0.01% = 1mV).

Table III - Life Test Endpoint and Delta Parameter (Product is tested in accordance with Table II with the following exceptions)								
D	Symbol	Sub-	Post Burn In Limit Pos		Post Life	Post Life Test Limit		Units
Parameter	Symbol	groups	Min	Max	Min	Max	Test Delta	Units
Relative Accuracy	R <sub>A</sub>	1		±1.1		±1.2	±0.1	%FS

# 5.0 <u>Life Test/Burn-In Information</u>

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
Α	Initiate	20-NOV-01
В	Update web address	Jan. 25, 2002
С	Update 1.0 Scope description.	26 July 2007
D	Update header/footer and add to 1.0 scope description.	Feb. 29,2008
Е	Add Junction Temperature (T <sub>J</sub> ) 150°C to Absolute Maximum Ratings	April 3, 2008
F	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	5-JUN-2009
G	Updated fonts and sizes to ADI standards. Update Die picture	01-Nov-2011